



DMPH4023SK3

Product Summary

BV _{DSS}	R _{DS(ON)} max	l _D max T _C = +25°C
-40V	26mΩ @ V_{GS} = -10V	-50A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment

40V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Features

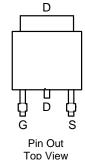
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMPH4023SK3Q</u>)

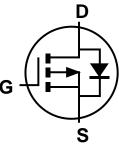
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



Top View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4023SK3-13	TO252 (DPAK)	2,500/Tape & Reel

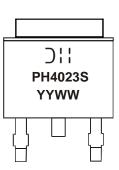
EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



) | | = Manufacturer's Marking
 PH4023S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 17 = 2017)
 WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = -10V	T _C = +25°C T _C = +100°C	ID	-50 -35	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-70	A
Maximum Continuous Body Diode Forward Current (Note 6)	ls	-4	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	-70	A	
Avalanche Current, L = 0.1mH (Note 7)	I _{AS}	-40	A	
Avalanche Energy, L = 0.1mH (Note 7)	E _{AS}	85	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)		PD	2.1	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	71	°C/W	
Total Power Dissipation (Note 6)		PD	3.6	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	41	80 M/	
Thermal Resistance, Junction to Case		R ₀ JC	1.5	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			, ,,				
Drain-Source Breakdown Voltage	BV _{DSS}	-40		—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		21	26	mΩ	$V_{GS} = -10V, I_D = -10A$	
Diode Forward Voltage	V _{SD}	_	-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		1091	—	pF		
Output Capacitance	C _{oss}		288	_	рF	V _{DS} = -20V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss		111	—	pF		
Gate Resistance	R _g		14	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg		18.7	—	nC	$V_{DS} = -20V, I_{D} = -10A,$	
Gate-Source Charge	Q _{gs}	_	4.2	—	nC	55 / 5 /	
Gate-Drain Charge	Q _{gd}	_	5.0	—	nC	V _{GS} = -10V	
Turn-On Delay Time	t _{D(ON)}	_	5.3	—	ns		
Turn-On Rise Time	t _R	_	4.8	_	ns	$V_{DD} = -20V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	30.7	—	ns	$R_{G} = 6\Omega, I_{D} = -10A$	
Turn-Off Fall Time	tF	_	23.4	—	ns	7	
Reverse Recovery Time	t _{RR}	_	17.8	—	ns		
Reverse Recovery Charge	Q _{RR}	_	9.2	—	nC	I _F = -10A, di/dt = -100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

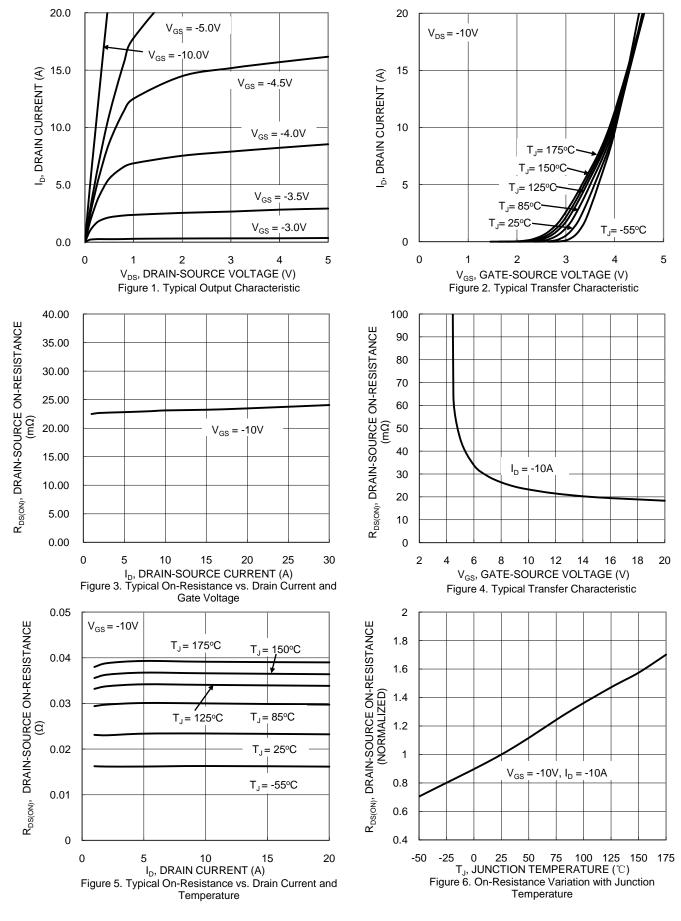
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{\rm J}$ = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

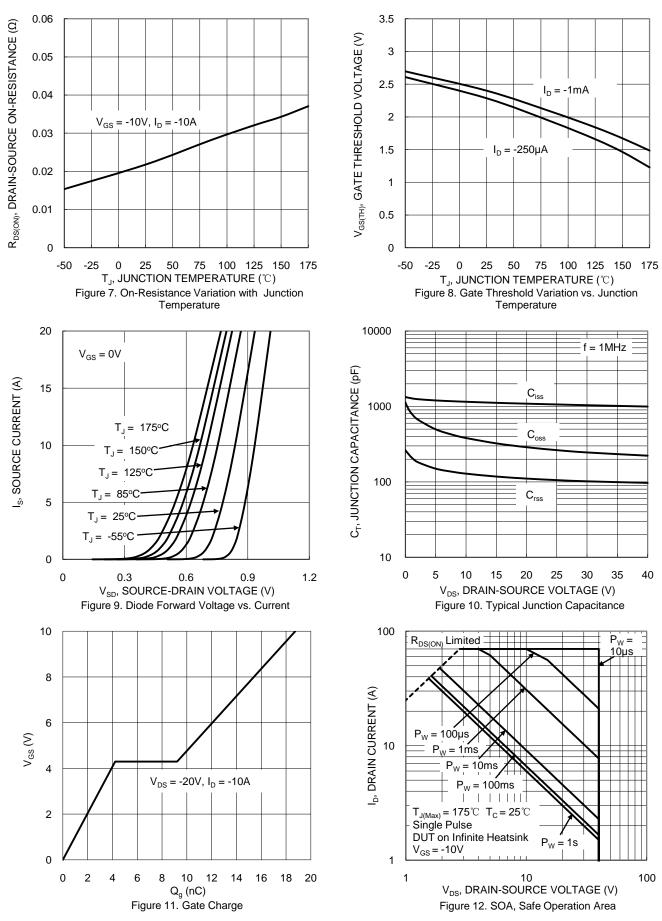


DMPH4023SK3



DMPH4023SK3 Document number: DS38134 Rev. 1 - 2

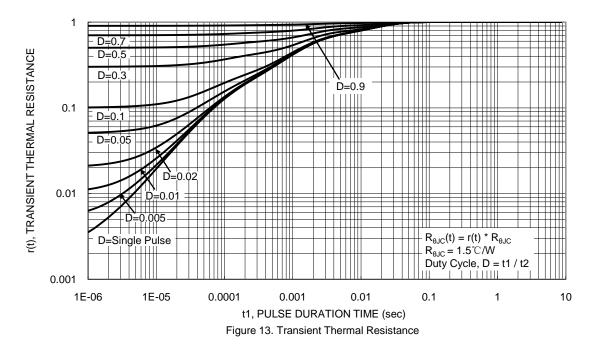




DMPH4023SK3 Document number: DS38134 Rev. 1 - 2 4 of 7
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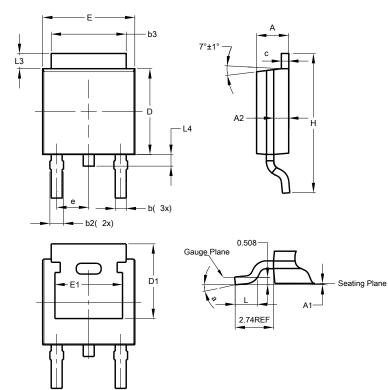




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

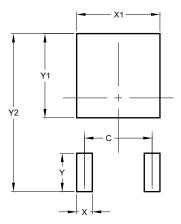


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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